

"RESPONSE UNDER 37 CFRREGEIVED
EXPEDITED PROSPOURE EXAMINING 2003
GROUP_3813 _" FEB -7 2003

Docket No.: 207224US0 TC 2800 HAIL ROOM

OBLON
SPIVAK
MCCLELLAND
MAIER
A
NEUSTADT
BC.

ASSISTANT COMMISSIONER FOR PATENTS WASHINGTON, D.C. 20231

ATTORNEYS AT LAW

RE: Application Serial No.: 09/846,255

Applicants: Satoshi KIKUCHI, et al.

Filing Date: May 2, 2001

For: CLEANING PROCESS FOR SUBSTRATE SURFACE

Group Art Unit: 2813
Examiner: L. Schillinger

SIR:

Attached hereto for filing are the following papers:

AMENDMENT UNDER 37 CFR 1.116 (WITH MARKED-UP COPY)

Our check in the amount of \$0.00 is attached covering any required fees. In the event any variance exists between the amount enclosed and the Patent Office charges for filing the above-noted documents, including any fees required under 37 C.F.R 1.136 for any necessary Extension of Time to make the filing of the attached documents timely, please charge or credit the difference to our Deposit Account No. 15-0030. Further, if these papers are not considered timely filed, then a petition is hereby made under 37 C.F.R. 1.136 for the necessary extension of time. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,

MAIER & NEUSTADT, P.C.

Norman F. Oblon

Registration No. 24,618

Harris A. Pitlick

Registration No. 38,779

22850

(703) 413-3000 (phone) (703) 413-2220 (fax)



"RESPONSE UNDER 37 CFR 1.116-EXPEDITED PROGEDURE EXAMINING RFCEIVED

FEB -7 2003

IN THE UNITED STATES PATENT & TRADEMARK OFFICE AIL ROOM

IN RE APPLICATION OF

SATOSHI KIKUCHI ET AL

SERIAL NO: 09/846,255

FILED: MAY 2, 2001

FOR: CLEANING PROCESS FOR

SUBSTRATE SURFACE

: EXAMINER: SCHILLINGER, L.

: GROUP ART UNIT: 2813

#10/B Andt AHE J.M.Chinller 3/4/03

AMENDMENT UNDER 37 CFR 1.116

ASSISTANT COMMISSIONER FOR PATENTS WASHINGTON, D.C. 20231

SIR:

Responsive to the Final Office Action dated November 6, 2002, Applicants respectfully request reconsideration of the above-identified application in view of the following amendment and remarks.

IN THE SPECIFICATION

Please replace the paragraph at page 44, lines 5-18 as follows:

100 B

--Although the tolerance of a loss differs depending on the device or step, a thermal oxide film is widely used, for example, as a gate oxide film or the like in many instances, and a loss may be considered to be acceptable if it is 0.1 nm (1 Å) or so when the thermal oxide film is 10 nm (100 Å) in thickness. Nonetheless, the loss in this Comparative Example was not considered to be sufficient when compared with the loss in Example 1. It has, therefore, been found that the conditions used in this Comparative Example are not considered to be